2-Bit 100 Mb/s Configurable Dual-Supply Level Translator

The NLSX3012 is a 2-bit configurable dual-supply bidirectional level translator without a direction control pin. The I/O $V_{CC}-$ and I/O $V_{L}-$ ports are designed to track two different power supply rails, V_{CC} and V_{L} respectively. The V_{CC} supply rail is configurable from 1.3 V to 4.5 V while the V_{L} supply rail is configurable from 0.9 V to ($V_{CC}-0.4$) V. This allows lower voltage logic signals on the V_{L} side to be translated into higher voltage logic signals on the V_{CC} side, and vice–versa. Both I/O ports are auto–sensing; thus, no direction pin is required.

The Output Enable (EN) input, when Low, disables both I/O ports by putting them in 3–state. This significantly reduces the supply currents from both V_{CC} and V_L . The EN signal is designed to track V_L .

Features

- Wide High–Side V_{CC} Operating Range: 1.3 V to 4.5 V Wide Low–Side V_L Operating Range: 0.9 V to $(V_{CC}$ 0.4) V
- \bullet High-Speed with 140 Mb/s Guaranteed Date Rate for $V_L > 1.8 \text{ V}$
- Low Bit-to-Bit Skew
- Overvoltage Tolerant Enable and I/O Pins
- Non-preferential Powerup Sequencing
- Small packaging: UDFN8, SO-8, Micro8
- These are Pb-Free Devices

Typical Applications

- Mobile Phones, PDAs, Other Portable Devices
- PC and Laptops



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MARKING DIAGRAMS



UDFN8 MU SUFFIX CASE 517AJ



VA = Specific Device Code

M = Date Code

= Pb-Free Package



SO-8 D SUFFIX CASE 751



A = Assembly Location

L = Wafer Lot Y = Year

Y = Year W = Work Week

= Pb-Free Package



Micro8 DM SUFFIX CASE 846A



A = Assembly Location

Y = Year

W = Work Week

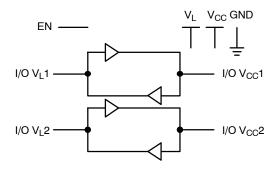
= Pb-Free Package

ORDERING INFORMATION

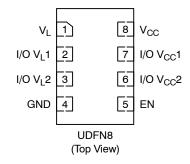
Device	Package	Shipping [†]
NLSX3012MUTAG	UDFN8 (Pb-Free)	3000/Tape & Reel
NLSX3012DR2G	SO-8 (Pb-Free)	2500/Tape & Reel
NLSX3012DMR2G	Micro8 (Pb-Free)	4000/Tape & Reel

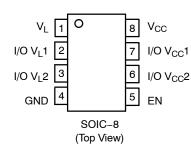
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

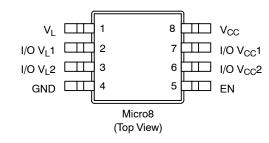
LOGIC DIAGRAM



PIN ASSIGNMENTS







PIN ASSIGNMENT

Pins	Description
V _{CC}	V _{CC} Input Voltage
V _L	V _L Input Voltage
GND	Ground
EN	Output Enable
I/O V _{CC} n	I/O Port, Referenced to V _{CC}
I/O V _L n	I/O Port, Referenced to V _L

FUNCTION TABLE

EN	Operating Mode
L	Hi–Z
Н	I/O Buses Connected

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CC}	V _{CC} Supply Voltage	-0.5 to +5.5		V
V_L	V _L Supply Voltage	-0.5 to +5.5		V
I/O V _{CC}	V _{CC} -Referenced DC Input/Output Voltage	-0.5 to (V _{CC} + 0.3)		V
I/O V _L	V _L -Referenced DC Input/Output Voltage	-0.5 to (V _L + 0.3)		V
V _{EN}	Enable Control Pin DC Input Voltage	-0.5 to +5.5		V
I _{IK}	Input Diode Clamp Current	-50	V _I < GND	mA
lok	Output Diode Clamp Current	-50	V _O < GND	mA
I _{CC}	DC Supply Current Through V _{CC}	±100		mA
IL	DC Supply Current Through V _L	±100		mA
I _{GND}	DC Ground Current Through Ground Pin	±100		mA
T _{STG}	Storage Temperature	-65 to +150		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Symbol Parameter		Min	Max	Unit
V _{CC}	V _{CC} Supply Voltage		1.3	4.5	V
V_L	V _L Supply Voltage		0.9	V _{CC} - 0.4	V
V _{EN}	Enable Control Pin Voltage		GND	4.5	V
V _{IO}	Bus Input/Output Voltage	I/O V _{CC} I/O V _L	GND GND	4.5 4.5	V
T _A	Operating Temperature Range		-40	+85	°C
ΔΙ/ΔV	Input Transition Rise or Rate V _I , V _{IO} from 30% to 70% of V _{CC} ; V _{CC} = 3.3 V \pm 0.3 V		0	10	ns

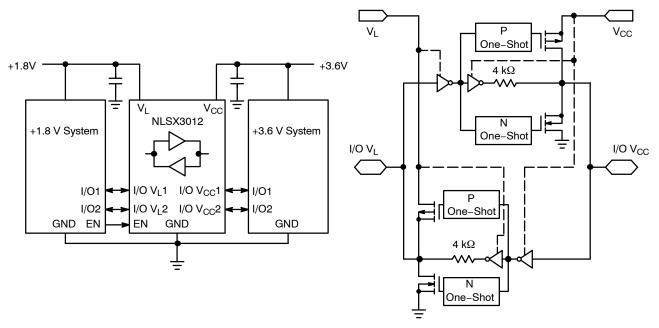


Figure 1. Typical Application Circuit

Figure 2. Simplified Functional Diagram (1 I/O Line) (EN = 1)

DC ELECTRICAL CHARACTERISTICS

					-4	0°C to +85	5°C	
Symbol	Parameter	Test Conditions (Note 1)	V _{CC} (V) (Note 2)	V_L (V) (Note 3)	Min	Typ (Note 4)	Max	Unit
V _{IHC}	I/O V _{CC} Input HIGH Voltage		1.3 to 4.5	0.9 to (V _{CC} – 0.4)	0.8 * V _{CC}	-	_	V
V _{ILC}	I/O V _{CC} Input LOW Voltage		1.3 to 4.5	0.9 to (V _{CC} – 0.4)	-	-	0.2 * V _{CC}	V
V _{IHL}	I/O V _L Input HIGH Voltage		1.3 to 4.5	0.9 to (V _{CC} – 0.4)	0.8 * V _L	-	-	V
V _{ILL}	I/O V _L Input LOW Voltage		1.3 to 4.5	0.9 to (V _{CC} – 0.4)	-	-	0.2 * V _L	V
V _{IH}	Control Pin Input HIGH Voltage	T _A = +25°C	1.3 to 4.5	0.9 to (V _{CC} – 0.4)	0.8 * V _L	-	-	V
V _{IL}	Control Pin Input LOW Voltage	T _A = +25°C	1.3 to 4.5	0.9 to (V _{CC} – 0.4)	-	-	0.2 * V _L	V
V _{OHC}	I/O V _{CC} Output HIGH Voltage	I/O V _{CC} Source Current = 20 μA	1.3 to 4.5	0.9 to (V _{CC} – 0.4)	0.8 * V _{CC}	-	-	V
V _{OLC}	I/O V _{CC} Output LOW Voltage	I/O V _{CC} Sink Current = 20 μA	1.3 to 4.5	0.9 to (V _{CC} – 0.4)	-	-	0.2 * V _{CC}	V
V _{OHL}	I/O V _L Output HIGH Voltage	I/O V _L Source Current = 20 μA	1.3 to 4.5	0.9 to (V _{CC} – 0.4)	0.8 * V _L	-	-	V
V _{OLL}	I/O V _L Output LOW Voltage	I/O V _L Sink Current = 20 μA	1.3 to 4.5	0.9 to (V _{CC} – 0.4)	-	-	0.2 * V _L	V

Normal test conditions are V_{EN} = 0 V, C_{IOVCC} = 15 pF and C_{IOVL} = 15 pF, unless otherwise specified.
 V_{CC} is the supply voltage associated with the high voltage port, and V_{CC} ranges from +1.3 V to 4.5 V under normal operating conditions.
 V_L is the supply voltage associated with the low voltage port. V_L must be less than or equal to (V_{CC} - 0.4) V during normal operation. However, during startup and shutdown conditions, V_L can be greater than (V_{CC} - 0.4) V.
 Typical values are for V_{CC} = +2.8 V, V_L = +1.8 V and T_A = +25°C. All units are production tested at T_A = +25°C. Limits over the operating temperature range are guaranteed by design.

POWER CONSUMPTION

	Test Conditions	V _{CC} (V)	$V_{CC}(V)$ $V_{L}(V)$	-40°C to +85°C				
Symbol	Parameter	(Note 5)	(Note 6)	(Note 7)	Min	Тур	Max	Unit
I _{Q-VCC}	Supply Current from V _{CC}	$ \begin{split} &EN = V_{L;} \text{ I/O } V_{CCn} = 0 \text{ V, I/O } V_{Ln} = 0 \text{ V,} \\ &I/O V_{CCn} = V_{CC} \text{ or I/O } V_{Ln} = V_{L} \text{ and } I_{o} = 0 \end{split} $	1.3 to 3.6	0.9 to (V _{CC} – 0.4)	-	-	1.0	μΑ
I _{Q-VL}	Supply Current from V _L	$ \begin{split} &EN = V_{L;} \text{ I/O } V_{CCn} = 0 \text{ V, I/O } V_{Ln} = 0 \text{ V,} \\ &I/O V_{CCn} = V_{CC} \text{ or I/O } V_{Ln} = V_{L} \text{ and } I_{o} = 0 \end{split} $	1.3 to 3.6	0.9 to (V _{CC} – 0.4)	-	-	1.0	μА
		$ \begin{split} & EN = V_L, I/O V_{CCn} = 0 V, I/O V_{Ln} = 0 V, \\ & I/O V_{CCn} = V_{CC} \text{or} I/O V_{Ln} = (V_{CC} - 0.2 V) \text{and} I_0 = 0 \end{split} $		< (V _{CC} – 0.2)	-	-	2.0	
I _{TS-VCC}	V _{CC} Tristate Output Mode Supply Current	EN = 0 V	1.3 to 3.6	0.9 to (V _{CC} – 0.4)	-	-	1.0	μΑ
I _{TS-VL}	V _L Tristate Output Mode Supply	EN = 0 V	1.3 to 3.6	0.9 to (V _{CC} – 0.4)	-	-	0.2	μА
	Current	EN = 0 V		V _{CC} – 0.2	-	-	2.0	
I _{OZ}	I/O Tristate Output	EN = 0 V	1.3 to 3.6	0.9 to (V _{CC} – 0.4)	_	-	0.15	μΑ
	Mode Leakage Current	EN = 0 V		V _{CC} – 0.2	_	-	2.0	
I _{EN}	Output Enable Pin Input Current	-	1.3 to 3.6	0.9 to (V _{CC} – 0.4)	-	-	1.0	μΑ

Normal test conditions are V_{EN} = 0 V, C_{IOVCC} = 15 pF and C_{IOVL} = 15 pF, unless otherwise specified.
 V_{CC} is the supply voltage associated with the high voltage port, and V_{CC} ranges from +1.3 V to 4.5 V under normal operating conditions.
 V_L is the supply voltage associated with the low voltage port. V_L must be less than or equal to (V_{CC} – 0.4) V during normal operation. However, during startup and shutdown conditions, V_L can be greater than (V_{CC} – 0.4) V.
 Typical values are for V_{CC} = +2.8 V, V_L = +1.8 V and T_A = +25°C. All units are production tested at T_A = +25°C. Limits over the operating temperature range are guaranteed by design.

TIMING CHARACTERISTICS

					-4	10°C to +85°	°C	
Symbol	Parameter	Test Conditions (Note 9)	V _{CC} (V) (Note 10)	V _L (V) (Note 11)	Min	Typ (Note 12)	Max	Unit
t _{R-VCC}	I/O V _{CC} Rise Time (Output = I/O_V _{CC})	C _{IOVCC} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		0.7	2.4	ns
t _{F-VCC}	I/O V _{CC} Falltime (Output = I/O_V _{CC})	C _{IOVCC} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		0.5	1.0	ns
t _{R-VL}	I/O V _L Risetime (Output = I/O_V _L)	C _{IOVL} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		1.0	3.8	ns
t _{F-VL}	I/O V _L Falltime (Output = I/O_V _L)	C _{IOVL} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		0.6	1.2	ns
Z _{O-VCC}	I/O V _{CC} One-Shot Output Impedance		1.3 to 4.5	0.9 to (V _{CC} – 0.4)		30		Ω
Z _{O-VL}	I/O V _L One-Shot Output Impedance		1.3 to 4.5	0.9 to (V _{CC} – 0.4)		30		Ω
t _{PD_VL-VCC}	Propagation Delay (Output = I/O_V _{CC} , t _{PHL} , t _{PLH})	C _{IOVCC} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		4.5	12	ns
t _{PD_VCC-VL}	Propagation Delay (Output = I/O_V _L , t _{PHL} , t _{PLH})	C _{IOVL} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		3.0	7.2	ns
t _{SK VL-VCC}	Channel-to-Channel Skew (Output = I/O_V _{CC})	C _{IOVCC} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		0.2	0.3	nS
t _{SK_VCC-VL}	Channel-to-Channel Skew (Output = I/O_V _L)	C _{IOVCC} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		0.2	0.3	nS
MDR	Maximum Data Rate	(Output = I/O_V _{CC} , C _{IOVCC} = 15 pF)	1.3 to 4.5	0.9 to (V _{CC} – 0.4)	110			Mb/s
		(Output = I/O_V_L , $C_{IOVL} = 15 pF$)	> 2.2	> 1.8	140			

^{9.} Normal test conditions are V_{EN} = 0 V, C_{IOVCC} = 15 pF and C_{IOVL} = 15 pF, unless otherwise specified.

10. V_{CC} is the supply voltage associated with the high voltage port, and V_{CC} ranges from +1.3 V to 4.5 V under normal operating conditions.

11. V_L is the supply voltage associated with the low voltage port. V_L must be less than or equal to (V_{CC} – 0.4) V during normal operation. However, during startup and shutdown conditions, V_L can be greater than (V_{CC} – 0.4) V.

12. Typical values are for V_{CC} = +2.8 V, V_L = +1.8 V and T_A = +25°C. All units are production tested at T_A = +25°C. Limits over the operating temperature range are guaranteed by design.

ENABLE / DISABLE TIME MEASUREMENTS

					-40°C to +85°C			
Symbol	Parameter	Test Conditions (Note 13)	V _{CC} (V) (Note 14)	V_L (V) (Note 15)	Min	Typ (Note 16)	Max	Unit
t _{EN-VCC}	Turn-On Enable Time (Output = I/O_V _{CC} , t _{pZH})	C _{IOVCC} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		150	200	ns
	Turn-On Enable Time (Output = I/O_V _{CC} , t _{pZL})	C _{IOVL} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		130	180	ns
t _{EN-VL}	Turn-On Enable Time (Output = I/O_V _L , t _{pZH})	C _{IOVCC} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		95	225	ns
	Turn-On Enable Time (Output = I/O_V _L , t _{pZL})	C _{IOVL} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		75	100	ns
t _{DIS-VCC}		C _{IOVCC} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		175	250	ns
	Propagation Delay (Output = I/O_V _{CC} , t _{PLZ})	C _{IOVL} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		140	160	ns
t _{DIS-VL}	Turn-Off Disable Time (Output = I/O_V _L , t _{pHZ})	C _{IOVCC} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		180	275	ns
	Propagation Delay (Output = I/O_V _L , t _{PLZ})	C _{IOVL} = 15 pF	1.3 to 4.5	0.9 to (V _{CC} – 0.4)		160	220	ns

- 13. Normal test conditions are V_{EN} = 0 V, C_{IOVCC} = 15 pF and C_{IOVL} = 15 pF, unless otherwise specified.

 14. V_{CC} is the supply voltage associated with the high voltage port, and V_{CC} ranges from +1.3 V to 4.5 V under normal operating conditions.

 15. V_L is the supply voltage associated with the low voltage port. V_L must be less than or equal to (V_{CC} 0.4) V during normal operation. However, during startup and shutdown conditions, V_L can be greater than (V_{CC} 0.4) V.

 16. Typical values are for V_{CC} = +2.8 V, V_L = +1.8 V and T_A = +25 °C. All units are production tested at T_A = +25 °C. Limits over the operating
- temperature range are guaranteed by design.

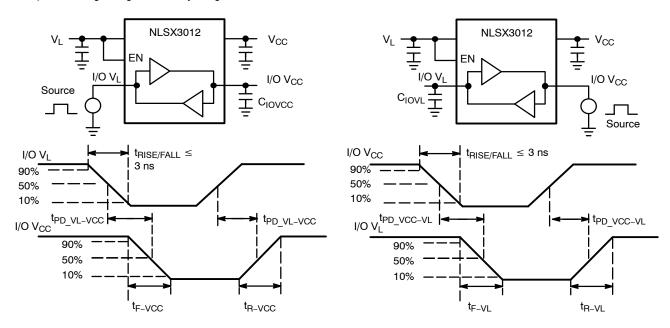
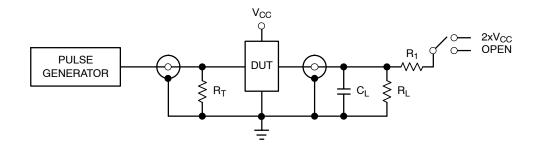


Figure 3. Driving I/O V_L Test Circuit and Timing

Figure 4. Driving I/O V_{CC} Test Circuit and Timing



Test	Switch
t _{PZH} , t _{PHZ}	Open
t _{PZL} , t _{PLZ}	2 x V _{CC}

 C_L = 15 pF or equivalent (Includes jig and probe capacitance) R_L = R_1 = 50 k Ω or equivalent R_T = Z_{OUT} of pulse generator (typically 50 Ω)

Figure 5. Test Circuit for Enable/Disable Time Measurement

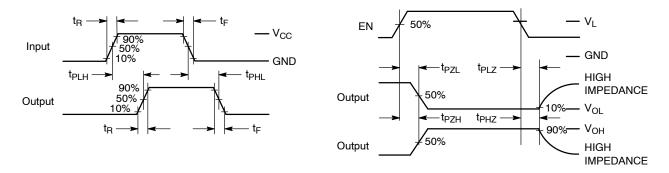


Figure 6. Timing Definitions for Propagation Delays and Enable/Disable Measurement

IMPORTANT APPLICATIONS INFORMATION

Level Translator Architecture

The NLSX3012 auto sense translator provides bi–directional voltage level shifting to transfer data in multiple supply voltage systems. This device has two supply voltages, V_L and V_{CC} , which set the logic levels on the input and output sides of the translator. When used to transfer data from the V_L to the V_{CC} ports, input signals referenced to the V_L supply are translated to output signals with a logic level matched to V_{CC} . In a similar manner, the V_{CC} to V_L translation shifts input signals with a logic level compatible to V_{CC} to an output signal matched to V_L .

The NLSX3012 consists of four bi-directional channels that independently determine the direction of the data flow without requiring a directional pin. The one-shot circuits are used to detect the rising or falling input signals. In addition, the one shots decrease the rise and fall time of the output signal for high-to-low and low-to-high transitions.

Input Driver Requirements

Auto sense translators such as the NLSX3012 have a wide bandwidth, but a relatively small DC output current rating. The high bandwidth of the bi-directional I/O circuit is used to quickly transform from an input to an output driver and vice versa. The I/O ports have a modest DC current output specification so that the output driver can be over driven when data is sent to in the opposite direction.

For proper operation, the input driver to the auto sense translator should be capable of driving 2 mA of peak output current with an output impedance less than 25 Ω . The bi-directional configuration of the translator results in both input stages being active for a very short time period. Although the peak current from the input signal circuit is relatively large, the average current is small and consistent with a standard CMOS input stage.

Output Load Requirements

The NLSX3012 is designed to drive CMOS inputs. Resistive pullup or pulldown loads of less than 50 k Ω should not be used with this device. The NLSX3373 or NLSX3378 open–drain auto sense translators are alternate

translator options for an application such as the I²C bus that requires pullup resistors.

Enable Input (EN)

The NLSX3012 has an Enable pin (EN) that provides tri–state operation at the I/O pins. Driving the Enable pin to a low logic level minimizes the power consumption of the device and drives the I/O $V_{\rm CC}$ and I/O $V_{\rm L}$ pins to a high impedance state. Normal translation operation occurs when the EN pin is equal to a logic high signal. The EN pin is referenced to the $V_{\rm L}$ supply and has Over–Voltage Tolerant (OVT) protection.

Uni-Directional versus Bi-Directional Translation

The NLSX3012 can function as a non-inverting uni-directional translator. One advantage of using the translator as a uni-directional device is that each I/O pin can be configured as either an input or output. The configurable input or output feature is especially useful in applications such as SPI that use multiple uni-directional I/O lines to send data to and from a device. The flexible I/O port of the auto sense translator simplifies the trace connections on the PCB.

Power Supply Guidelines

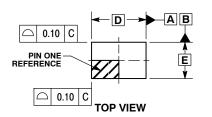
It is recommended that the V_L supply should be less than or equal to the value of the V_{CC} minus 0.4 V. The sequencing of the power supplies will not damage the device during the power up operation; however, the current consumption of the device will increase if V_L exceeds V_{CC} minus 0.4 V. In addition, the I/O V_{CC} and I/O V_L pins are in the high impedance state if either supply voltage is equal to 0 V.

For optimal performance, 0.01 to 0.1 μF decoupling capacitors should be used on the V_L and V_{CC} power supply pins. Ceramic capacitors are a good design choice to filter and bypass any noise signals on the power supply voltage lines to the ground plane of the PCB. The noise immunity will be maximized by placing the capacitors as close as possible to the supply and ground pins, along with minimizing the PCB connection traces.

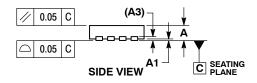
SCALE 4:1

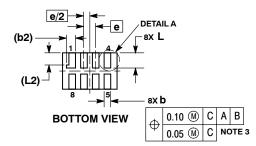


DATE 08 NOV 2006

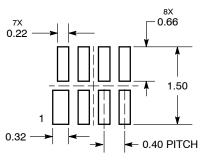








MOUNTING FOOTPRINT SOLDERMASK DEFINED



DIMENSIONS: MILLIMETERS

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSION & APPLIES TO PLATED
- DINICIPION D APPLIES TO PLATED
 TERMINAL AND IS MEASURED BETWEEN
 0.15 AND 0.30 mm FROM TERMINAL TIP.
 MOLD FLASH ALLOWED ON TERMINALS
 ALONG EDGE OF PACKAGE, FLASH MAY
 NOT EXCEED 0.03 ONTO BOTTOM
 SURFACE OF TERMINALS.
 DETAIL A SHOWS ODTIONAL
- DETAIL A SHOWS OPTIONAL CONSTRUCTION FOR TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.45	0.55		
A1	0.00	0.05		
A3	0.127	REF		
b	0.15	0.25		
b2	0.30	REF		
D	1.80	BSC		
E	1.20	BSC		
е	0.40	BSC		
L	0.45	0.55		
L1	0.00	0.03		
L2	0.40	REF		

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98AON23417D	Electronic versions are uncontrolled except when accessed directly from the Document Report Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	UDFN8 1.8X1.2, 0.4P		PAGE 1 OF 1		

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SOIC-8 NB CASE 751-07 **ISSUE AK**

DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
Н	0.10	0.25	0.004	0.010
7	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot

= Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww

= Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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STYLE 4: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 2 4. ANODE 5. ANODE #2 6. ANODE #2 7. ANODE #1 8. COMMON CATHODE
STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 STAGE Vd 7. EMITTER, #1 AGE Vd 8. COLLECTOR, #1
STYLE 12: 1 PIN 1. SOURCE 2 SOURCE 2 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COMMON 6. COLLECTOR, DIE #2 6. COMMON 7. COLLECTOR, DIE #1 6. COMMON 8. COLLECTOR, DIE #1
STYLE 20: 1 PIN 1. SOURCE (N) 2. GATE (N) 2 3. SOURCE (P) 4. GATE (P) 5. DRAIN 2 6. DRAIN 7. DRAIN 1 8. DRAIN
STYLE 24:
STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND E 5. V_MON E 6. VBULK E 7. VBULK 8. VIN

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DATE 16 JUL 2020







NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DDES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
- DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



RECOMMENDED MOUNTING FOOTPRINT

MID	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	-	-	1.10	
A1	0.05	0.08	0.15	
b	0.25	0.33	0.40	
С	0.13	0.18	0.23	
D	2.90	3.00	3.10	
E	2.90	3.00	3.10	
e	0.65 BSC			
HE	4.75	5.05		
L	0.40	0.55	0.70	

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code Α = Assembly Location

Υ = Year W = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. SOURCE	PIN 1. SOURCE 1	PIN 1. N-SOURCE
SOURCE	2. GATE 1	2. N-GATE
SOURCE	3. SOURCE 2	P-SOURCE
GATE	4. GATE 2	4. P-GATE
DRAIN	5. DRAIN 2	5. P-DRAIN
DRAIN	6. DRAIN 2	6. P-DRAIN
7. DRAIN	7. DRAIN 1	7. N-DRAIN
8. DRAIN	8. DRAIN 1	8. N-DRAIN

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